

#### Discrete POWER & Signal **Technologies**

# **NPDS8301 NPDS8302 NPDS8303**



# **N-Channel General Purpose Dual Amplifier**

Sourced from Process 83.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>DG</sub>	Drain-Gate Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	40	V
I <sub>GF</sub>	Forward Gate Current	10	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# **General Purpose Dual Amplifier**

(continued)

### **Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHARACTERISTICS						
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = 1.0 \mu\text{A},  V_{DS} = 0$	- 40		V	
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = 20 \text{ V}, V_{DS} = 0$		100	pА	
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	$V_{DS} = 20 \text{ V}, I_{D} = 1.0 \text{ nA}$	- 0.5	- 3.5	V	
$V_{GS}$	Gate-Source Voltage	$V_{DS} = 20 \text{ V}, I_D = 200 \mu\text{A}$	- 0.3	- 3.5	V	
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#### ON CHARACTERISTICS

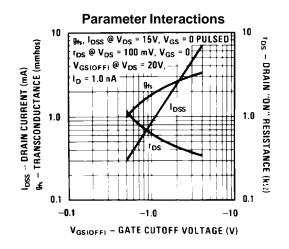
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current*	$V_{DS} = 20 \ V, V_{GS} = 0$	0.5	6.0	mA

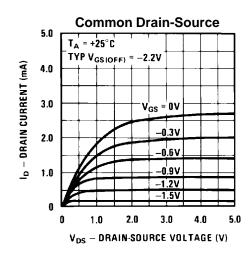
#### SMALL SIGNAL CHARACTERISTICS

9fs	Common Source Forward Transconductance	$V_{DS} = 20 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$ $V_{DS} = 20 \text{ V}, I_{D} = 200 \mu\text{A},$	1000 700	4000 1200	μmhos μmhos
	Tansconductance	$V_{DS} = 20 \text{ V}, I_D = 200 \mu\text{A},$ f = 1.0  kHz	700	1200	μππος
goss	Common Source Output Conductance	$V_{DS} = 20 \text{ V}, I_D = 200 \mu\text{A}, f = 1.0 \text{ kHz}$		20	μmhos
gos	Common Source Output Conductance	$V_{DS} = 20 \text{ V}, I_{D} = 200 \mu\text{A},$ f = 1.0 kHz		5.0	μmhos
V <sub>GS1</sub> - V <sub>GS2</sub>	Differential Match	$V_{DG} = 20 \text{ V}, I_D = 200 \mu\text{A},$			
		NPDS8301		5.0	mV
		NPDS8302		10	mV
		NPDS8303		15	mV
$\Delta V_{GS1}$ - $V_{GS2}$	Differential Drift	$V_{DS} = 20 \text{ V}, I_{D} = 200 \mu\text{A},$			
		$T_A = 25 \text{ to } 85 ^{\circ}\text{C}$ NPDS8301		10	μV/°C
		NPDS8302		15	μV/°C
		NPDS8303		25	μV/°C

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300 ms, Duty Cycle  $\leq$  2%

# **Typical Characteristics**

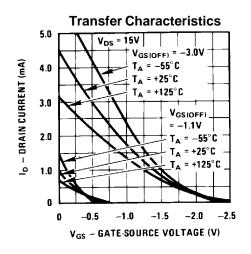


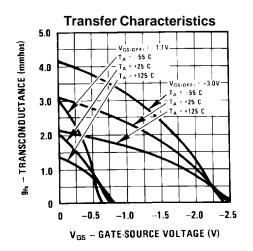


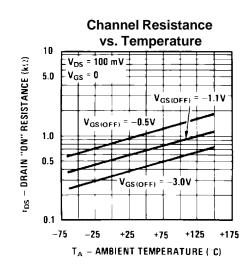
## **General Purpose Dual Amplifier**

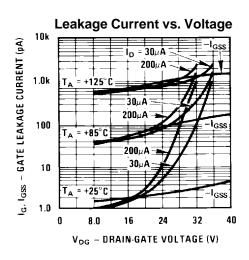
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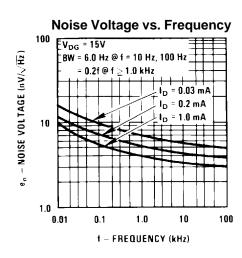
# Typical Characteristics (continued)

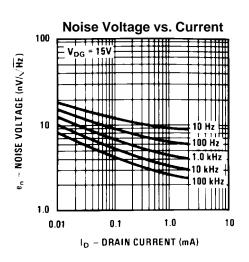












# **General Purpose Dual Amplifier**

(continued)

#### Typical Characteristics (continued)

